

DESCRIPTION

The NB639 is a fully integrated, high frequen cy synchronous rectif ied step-down switch mode converter. It offers a very compac t solution t o achieve 8A continuous output current over a wide input supply range with excellent load and line regulation. The NB639 operates at high efficiency over a wide output current load range.

To further optimize efficiency at light load, this device's V $_{\rm CC}$ supply is designed to be biased externally.

Constant-On-Time (COT) control mode provides fast transient response and eases loop stabilization.

Full protection features in clude SCP, OCP, OVP, UVP and thermal shutdown.

The NB639 requires a minimum number of readily available st andard external components and is available in a sp ace-saving QF N20 (3x4m m) package.

FEATURES

- Wide 4.5V to 28V Operating Input Range
- 8A Output Current
- Internal $30m\Omega$ High-Side, $12m\Omega$ Low-Side Power MOSFETs
- Proprietary Switching Loss Reduction Technique
- 1% Reference Voltage
- Programmable Soft Start Time
- Soft Shutdown
- Programmable Switching Frequency
- SCP, OCP, OVP, UVP Protection and Thermal Shutdown
- Output Adjustable from 0.8V to 13V
- Available in a QFN20 (3x4mm) Package

APPLICATIONS

- Notebook Systems and I/O Power
- Networking Systems
- Optical Communication Systems
- Distributed Power POL Systems

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TYPICAL APPLICATION

ORDERING INFORMATION

Part Number*	Package	Top Marking
NB639DL	QFN20 (3x4mm)	639

* For Tape & Reel, add suffix –Z (e.g. NB639DL–Z)

For RoHS compliant packaging, add suffix -LF (e.g. NB639DL-LF-Z)



ABSOLUTE MAXIMUM RATINGS (1)

Supply Voltage V _{IN}	30V
Supply Voltage V _{CC}	6V
V _{SW} C	$0.3V$ to $V_{IN} + 0.3V$
V _{BST}	V _{SW} + 6V
I _{VIN (RMS)}	3.5A
V _{PGOOD} C	0.3V to V _{CC} +0.6V
All Other Pins	0.3V to +6V
Continuous Power Dissipation	(T _A = +25°C) ⁽²⁾
	2.6W
Junction Temperature	150°C
Lead Temperature	260°C
Storage Temperature	-65°C to +150°C

Recommended Operating Conditions ⁽³⁾

Supply Voltage V _{IN}	4.5V to 28V
Supply Voltage V _{CC}	5V
Output Voltage Vout	0.8V to 13V
Operating Junction Temp. (T _J).	-40°C to +125°C

Thermal Resistance ⁽⁴⁾ *θ_{JA} θ_{JC}* QFN20 (3x4mm)......4810...°C/W

Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction tempe rature T J(MAX), the junction-to-ambient thermal resistance θ_{JA}, and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D(MAX)=(TJ(MAX)-T_A)/θ_{JA}. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal sh utdown. Internal thermal shutdo wn circuitr y protects the device from permanent damage.
- The device is not guarant eed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.

ELECTRICAL CHARACTERISTICS

V_{IN} = 12V, V_{CC} =5V, T_A = +25°C, unless otherwise noted.

Parameters	Symbol	Condition	Min	Тур	Max	Units
Input Supply Current (Shutdown)	I _{IN}	V _{EN} = 0V		0		μA
Input Supply Current (Quiescent)	I _{IN}	V _{EN} = 2V, V _{FB} = 1V		40		μA
V _{CC} Supply Current (Quiescent)	Ivcc V	_{EN} = 2V, V _{FB} = 1V		350		μA
HS Switch On Resistance (5) HS	RDS-ON			30		mΩ
LS Switch On Resistance ⁽⁵⁾ LS	RDS-ON			12		mΩ
Switch Leakage	SW _{LKG}	$V_{EN} = 0V$, $V_{SW} = 0V$ or 12V	0		10	μA
Current Limit	I _{LIMIT}			16.5		А
One-Shot On Time	T _{ON}	R_{FREQ} =348kΩ, V _{OUT} =1.05V	360			ns
Minimum Off Time ⁽⁵⁾	T _{OFF}			100		ns
Fold-back Off Time ⁽⁵⁾	T _{FB}	I _{LIM} =1 (HIGH)		7.5		μs
OCP hold-off time ⁽⁵⁾	T _{oc}	I _{LIM} =1 (HIGH)			40	μs
Feedback Voltage	V _{FB}		807 8 ⁻	15	823 m	/
Feedback Current	I _{FB}	V _{FB} = 815mV		10	50	nA
Soft Start Charging Current	+I _{SS}	V _{SS} =0V		8.5		μA
Soft Stop Discharging Current	-I _{SS}	V _{SS} =0.815V		8.5		μA
Power Good Rising Threshold	PGOOD _{Vth⁻Hi}			0.9		V_{FB}
Power Good Falling Threshold	PGOOD _{Vth⁻Lo}			0.85		V_{FB}
Power Good Rising Delay	T _{PGOOD}	Tss = 1ms			1	ms
Power Good Rising Delay	T _{PGOOD}	Tss = 2ms			1.5	ms
Power Good Rising Delay	T _{PGOOD}	Tss = 3ms			2	ms
EN Rising Threshold	EN_{Vth}		1.05	1.35	1.60	V
EN Threshold Hysteresis	$EN_{Vth-Hys}$		250	420	550 m`	/
EN Input Current	I _{EN}	V _{EN} = 2V		2		μA
V _{CC} Under-Voltage Lockout Threshold Rising	$V_{\text{CC}}UV_{\text{Vth}}$		3.8	4.0	4.2	V
V _{CC} Under-Voltage Lockout Threshold Hysteresis	$V_{CC}UV_{HYS}$			880		mV
V _{OUT} Over-Voltage Protection Threshold	V _{OVP}			1.25		V_{FB}
V _{OUT} Under-Voltage Detection Threshold	V _{UVP}			0.7		V_{FB}
Thermal Shutdown	T _{SD}			150		°C
Thermal Shutdown Hysteresis	T _{SD-HYS}			25		°C

Notes:

5) Guaranteed by design.

PIN FUNCTIONS

Pin #	Name	Description
1 AGND		Analog Ground.
2 FREQ		Frequency Set during CCM operation. The ON period is determined by the input voltage and the frequency-set resistor connected to FREQ pin. Connect a resistor to IN for line feed-forward. Decouple with a 1nF capacitor.
3 FB		Feedback. An external resistor divider from the output to GND, tapped to the FB pin, sets the output voltage.
4 SS		Soft Start. Connect an external SS capacitor to program the soft start time for the switch mode regulator. When the EN pin becomes high, an internal current source (8.5uA) charges up the SS capacitor and the SS voltage slowly ramps up from 0 to V_{FB} smoothly. When the EN pin becomes low, an internal current source (8.5µA) discharges the SS capacitor and the SS voltage slowly ramps down.
5 EN		EN=1 to enable the NB639. For automatic start-up, connect EN pin to IN with a $100k\Omega$ resistor. It includes an internal $1M\Omega$ pull-down resistor.
6	PGOOD	Power Goo d Output. The output of this pin i s an o pen d rain a nd is hig h if the output voltage is higher than 90% of the nominal voltage. There is delay from FB \ge 90% to PGOOD high, which is 50% of SS time plus 0.5ms.
7 BST		Bootstrap. A capacitor connected between SW and BS pins is required to form a floating supply across the high-side switch driver.
8, 19	IN	Supply Voltage. The NB639 operates from a +4.5V to +28V input rail. C1 is needed to decouple the input rail. Use wide PCB traces and multiple vias to make the connection.
9, 10, 17, 18	SW	Switch Output. Use wide PCB traces and multiple vias to make the connection.
11-16 PGND		System Ground. This pin is the reference ground of the regulated output voltage. For this reason care must be taken in PCB layout.
20 VCC		External 5V Supply. This 5V supply has to be applied in order to bias the device. Decouple with a 1μ F capacitor as close to this pin as possible.

TYPICAL PERFORMANCE CHARACTERISTICS

 V_{IN} =12V, V_{OUT} =1.05V, L=1.0µH, T_A=+25°C, unless otherwise noted.



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TYPICAL PERFORMANCE CHARACTERISTICS (continued) V_{IN}=12V, V_{OUT} =1.05V, L=1.0µH, T_A=+25°C, unless otherwise noted. Input & Output Voltage Ripple Input & Output Voltage Ripple Input & Output Voltage Ripple I_{OUT} = 4mA I_{OUT} = 0.5A I_{OUT} = 8A V_{OUT} 50mV/div. V_{OUT} 50mV/div. V_{OUT} 50mV/div. V_{IN} 200mV/div. V_{IN} 200mV/div. V_{IN} 200mV/div. V_{SW} 10V/div. V_{SW} 10V/div. V_{SW} 10V/div. IL. ا 5A/div Ι_L 5A/div. 2A/div. 2ms/div. 2µs/div. 1µs/div. **Power Good** Start-Up Through VIN **Power Good** Through VIN Start-Up Through VIN Shutdown $I_{OUT} = 0A$ I_{OUT} = 8A I_{OUT} = 8A VOUT V_{OUT} 500mV/div. VOUT 500mV/div. 500mV/div. V_{IN} 10V/div. V_{IN} 10V/div. V_{IN} 5V/div. V_{SW} 20V/div. PG PG 5V/div. 5V/div ا 2A/div 1ms/div. 100µs/div. 2ms/div. Start-Up Through VIN Shutdown Through VIN Shutdown Through VIN I_{OUT} = 8A $I_{OUT} = 0A$ I_{OUT} = 8A V_{OUT} 500mV/div. V_{OUT} 500mV/div. V_{OUT} 500mV/div. V_{IN} 10V/div. V_{IN} 5V/div. E V_{IN} 5V/div. V_{SW} 20V/div. V_{SW} 20V/div. V_{SW} 5V/div. ا 10A/div. IL 10A/div. ΙL 2A/div 2ms/div. 10ms/div. 40µs/div.





BLOCK DIAGRAM



Figure 1—Functional Block Diagram

OPERATION

PWM Operation

The NB639 is a fully integrated synchronous rectified step-down switch mode converter. Constant-on-time (COT) control is employed to provide fast transient response and easy loop stabilization. At the beginning of each cycle, the high-side MOSFET (HS-FET) is turned on when the feedback voltage (V_{FB}) is below the reference voltage (V_{REF}) which indicates insufficient output voltage. The ON period is determined by the input voltage and the frequency-set resistor as follows:

$$T_{\text{(N)}} \text{ ns)} = \frac{12 \times \mathbf{R}_{\text{FREQ}}(k)}{V_{\text{(k)}} V - 0.4}$$
(1)

After the ON period elapses, the HS-FET is turned off, or becomes OFF state. It is turned ON again when V _{FB} drops below V_{REF}. By repeating operation th is way, the converter r egulates th e output voltage. The integrated low-side MOSFET (LS-FET) is turned on when the HS-FET is in it s OFF state to minimize the conduction loss. The re will be a de ad short be tween input and GND i f both HS-FET and LS-FET are turned on at th e same time. It's called shoot-through. In order to avoid shoot-through, a dead-time (DT) is internally generated between HS-FET off and LS-FET on, or LS-FET off and HS-FET on.

Heavy-Load Operation



As Figure 2 shows, when the outp ut current is high, the HS-FET and LS-FET repeat on/off as described a bove. In this operation, the inducto r current will never go to zero. It's calle d continuous-conduction-mode (CCM) operation. In CCM operation, the switching frequ ency (F_{SW}) is fairly constant.

Light-Load Operation

When the load current decreases. The NB639 reduces the switching frequency automatically to maintain high efficiency. The light load operation is shown in Figure 3. The V _{FB} does not reach V_{RFF} when the inductor current is approaching zero. As the output curr ent reduces from heavyload condition, the inductor current also decreases, and eventually comes close to zero. The LS-FET driver turns into tri-state (high Z) whenever the inductor current reaches zero level. A current modulator takes over the control of LS-FET and limits the ind uctor current to less th an 600µA. Hen ce, the output capacit ors dischar ge slowly to GND through LS-FET as well as R1 and R2. As a result, the efficiency at light load condition is greatly improved. At light lo ad condition, t he HS-FET is not tur ned ON a s frequently as at heavy load condition. This is called skip mode.



Figure 3—Light Load Operation

As the output current increases from the lig ht load condition, the time period within which t he current modulator regulates beco mes shorter. The HS-FET is turned on more frequently. Hence, the switching frequency increases correspondingly. The output current reaches the critical level when the current modulator time is zero. The critica I level of th e output current is d etermined as follows:

$$I_{OUT} = \frac{(V_{IN} - X_{OUT}) V_{OUT}}{2 \boxtimes \times F_{SW} \times V_{IN}}$$
(2)

It turns into PWM mode once the output current exceeds the critical level. After that, the switching frequency stays fairly constant over the output current range.

Switching Frequency

Constant-on-time (COT) control is used in the NB639 and there is no dedicated oscillator in the IC. The input voltage is feed-forwarded to the on-time one-shot timer through the resistor R $_{FREQ}$. The duty ra tio is kept as V $_{OUT}/V_{IN}$. Hence, the switching frequency is fairly con stant over t he input voltag e range. The switch ing frequency can be set as follows:

$$F_{\text{SW}} \text{ kHz}) = \frac{10^{\circ}}{\frac{12 \times \mathbf{R}_{\text{FREQ}}(k)}{V_{\text{IN}} \text{ V}) - 0.4} \times \frac{V_{\text{IN}} \text{ V}}{V_{\text{OUT}}(V)} T_{\text{DELAY}} \text{ ns})} (3)$$

Where T_{DELAY} is the comparator de lay. It's about 40ns.

Frequency vs. R_{FREQ}



NB639 is optimized to operate at high switching frequency with high e fficiency. High switchin g frequency makes it possible to utilize small size d LC filter components to save system PCB space.

RAMP Compensation

Figure 4 and Figure 5 show jitter occurring in both PWM mode and skip mode. When there is noise in the V_{FB} downward slope, the ON time o f the HS-FET driver de viates from its intende d location an d produces jitter. It is necessary to understand that there is a relationsh ip between a system's stability and t he steepne ss of the V_{FB} ripple's downward slope. The slope steepness of the V $_{\rm FB}$ ripple dominates in noise immunity. The magnitude of the V $_{\rm FB}$ ripple doesn't affect the noise immunity directly.



Figure 5—Jitter in Skip Mode

When the output capa citors are ceramic ones, the ESR ripple is not high enough to stabilize the system, an d external ramp compensation is needed.



Figure 6—Simplified Circuit in PWM Mode with External Ramp Compensation

In PWM mode, an equivalent circuit with HS-FET off and the use of an external ramp compensation circuit (R4, C4) is simplified in Figure 6. The external ramp is derived from the inductor rip ple current. If one chooses C4, R1, and R2 to meet the following condition:

$$\frac{1}{2\pi \times F_{SW} \times C_4} < \frac{1}{5} \times \left(\frac{R_1 \times R_2}{R_1 + R_2}\right)$$
(4)

Then one can have:

$$I_{R4} = +_{C4} \quad I_{FB} \approx I_{C4} \tag{5}$$

The downward slope of the V $_{\mbox{\scriptsize FB}}$ ripple can be estimated as:

$$V_{SLOPE1} = \frac{-V_{OUT}}{R4 \times C4}$$
(6)

As one can see from equation (6), if there is instability in PWM mode, one can reduce eith er R4 or C4. If C4 can not be reduced further due to limitation from equation (4), then one can only reduce R4. From bench experiment s, VSLOPE1 is expected to be around 20~40V/ms.

In the case of POSCAP or other types of capacitor with higher E SR, the external ramp is not necessary.



Figure 7—Simplified Circuit in PWM Mode without External Ramp Compensation

Figure 7 sh ows the equivalent circuit in PWM mode with the HS-FET off an d without an external ramp circuit. The ESR ripple dominates the output ripple. The downward slope of the V $_{FB}$ ripple is:

$$V_{\text{SLOPE1}} = \frac{-ESR V_{\text{REF}}}{L}$$
(7)

From equation (7), o ne can see that the downward slope of V $_{FB}$ ripple is proportional to ESR/L. Therefore, it's necessary to know the minimum ESR value of the ou tput capacitor s when no external ramp is used. There is also a limitation w ith inductance in the scase. The smaller the inductance, the more stable it will be.

From our b ench experiments, it is recommend ed to keep VSLOPE1 around 15~30V/ms.

While in skip mode, the downward slope is not related to the external ramp.

In skip m ode, the downward slope of the V $_{FB}$ ripple is the same whether the external ramp is used or not. Figure 8 sh ows an equivalent circuit with HS-FET off and the current modulato r regulating the LS-FET. The down ward slope of the V_{FB} ripple can be determined as follows (I_{MOD} is ignored here):



Figure 8—Simplified Circuit in Skip Mode

To keep the system stable during light load condition, the values of the FB resistors should not be too big. It is recommended to keep the V_{SLOPE2} value around 0.4~0.8mV/ms. It should be noted that $_{IMOD}$ is excluded from the equation because it does not impact the system's stability at light load conditions.

Bootstrap Charging

The floating power MOSFET driver i s recommended to be powered by a n external V_{CC} through D2 as shown in Figure 9. This floatin g driver has its own UVL O protection. This UVLO's rising thre shold is 2.2 V with a hysteresis of 150mV. U1 will regulate to maintain BST voltage across C4 If (V_{CC}-V_{SW}) is less tha n 3.5V. The recommended external BST diode D2 is IN4148, and the BST cap C4 is $0.1 \sim 1 \mu$ F.





Soft Start/Stop

The NB63 9 employs soft start/stop (SS) mechanism to ensure smooth o utput during power-up and power shutdown. When the EN pin becomes high, an internal current source (8.5 µA) charges up the SS CAP. The SS CAP voltag е REF voltage to the PWM takes over the V comparator. The output voltage smoothly ramp s up with the SS voltage. Once the SS voltage reaches the same level as the REF voltage, it keeps ramping up while REF takes over the PWM comp arator. At this point, the soft sta rt finishes and it enters into steady state operation.

When the EN pin bec omes low, the SS CAP voltage is discharged t hrough an 8.5 μ A internal current sou rce. Once the SS voltage reache s REF voltage, it takes over the PWM comparator. The output voltage will decrease smoothly with SS voltage until zero le vel. The S S CAP value can be determined as follows:

$$C_{s} (nF) = \frac{T_{ss}(ms) \times I_{ss}(\mu A)}{V_{eF} (V)}$$
(9)

If the output capacitors have large capacitance value, it's n ot recommended to set the SS time too small. A minimal value of 4. 7nF should be used if the output capacitance value is large r than 330uF.

Power Good (PGOOD)

The NB639 has power -good (PGOOD) outp ut. The PGOOD pin is the open drain of a MOSFET. It should be connected to V $_{CC}$ or other volta ge source thro ugh a resistor (e.g. 10 0k). After the input voltage is applied, the MOSF ET is turned on, so that the PGOOD pin is pulled to GND before SS ready. After FB voltage reaches 90 %

of REF voltage, the PGOOD pin is pulled h igh after a delay.

The PGOOD delay time is determined as follows:

$$T_{PGOOD}(ms) = 0.5 \times T_{SS}(ms) + 0.5$$
 (10)

When the FB voltage drops to 85 % of the REF voltage, the PGOOD pin will be pulled low.

Over-Current Protection (OCP) and Sho rt-Circuit Protection (SCP)

The NB639 has cycle- by-cycle over-current limit control. The inductor current is monitored durin g the ON state. Once it detects that the inductor current is higher than the current limit, the HS-FET is turn ed off. At t he same time, the OCP timer is started. The OCP timer is set as 40 μ s. If in the following 40 μ s, the current limit is hit for every cycle, then it'll tri gger OCP. The converter needs power cycle to restart after it triggers OCP.

When the current limit is hit and the FB voltage is lower than 50% of the REF voltage, the devic e considers this as a dead short on the output and triggers OCP immediately. This is short circu it protection (SCP).

Over/Under-voltage Protection (OVP/UVP)

The NB639 monitors the output voltage through a resistor d ivider feedback (FB) volta ge to dete ct overvoltage and unde rvoltage on the output. When the FB voltage is higher than 125% of the REF v oltage, it'll trigg er O VP. Once it trigg ers OVP, the LS-FET is always on while the HS-FET is always off. It needs power cycle to power up again. When the FB vol tage is below 50% of the REF voltage (0.815V), UVP will be triggere d. Usually, UVP accompanies a h it in current limit and this results in SCP.

UVLO protection

The NB639 has under-voltage lock-out protection (UVLO). When V_{CC} is higher than the UVLO rising threshold voltage, the NB639 will be powered up. It shuts off when V_{CC} is lower than the UVLO falling threshold voltage. This is non-latch protection.

Thermal Shutdown

Thermal shutdown is employed in the NB639. The junction temperature of the IC is internally monitored. If the junction temperature exceeds the threshold value (typically 150°C), the converter shuts off. This is non-latch protection. There is about 25°C hysteresis. Once the junction temperature drops to around 125°C, it initiates a soft start.

APPLICATION INFORMATION

Setting the Output Voltage

The output voltage is set by using a resistor divider from the output voltage to FB pin.

When there is no external ramp employed, the output voltage is set by feedback resistors R1 and R2. First, choose a value for R2. A value within $5k\Omega$ -40k Ω is recommended to ensure stable operation. Then, R1 is determined as follows:

$$R1 = \frac{V_{OUT} - V_{REF}}{V_{REF}} R2$$
(11)

When low ESR ceramic capacitor is used in the output, an external voltage ramp should be added to FB through resistor R4 and capacit or C4. The output voltage is influen ced by ramp voltage V_{RAMP} except R divider. The V ramp can be calculated a s shown in equation 19. Choose a value within 5k Ω -40k Ω for R2. The value of R1 then is determined as follows:

$$R1 = \frac{1}{\frac{V_{REF}^{V} + \frac{1}{2} RAMP}{R2 \times (V_{OUT} V_{REF} - \frac{1}{2} V_{RAMP}}} - \frac{1}{R4}}$$
(12)

Using equation 12 to calculate the o utput voltage can be complicated. Furtherm ore, as V $_{\rm RAMP}$ changes due to changes in V_{OUT} and V_{IN}, V_{FB} also varies. To improve the output voltage accuracy and simplify the calculation of R2 in equation 12, a DC-blocking capacitor Cdc can be added.

Figure 10 shows a simplified cir cuit with extern al ramp compensation and a DC-blocking capacitor. With this capacitor, R1 can easily be obtained by using equation 11.

Cdc is sug gested to b e 1-4.7 μ F for better D C blocking performance.



Figure 10—Simplified Circuit with External Ramp Compensation and DC-Blocking Capacitor.

Input Capacitor

The input current to the step-down converter is discontinuous. Therefore, a capacitor is require d to supply the AC current to the step-down converter while maintaining the DC input voltage. Ceramic ca pacitors are recommen ded for best performance. In the layout, it's recommended to put the input capacitors as close to the IN pin as possible.

The capa citance varies significantly over temperature. Capacitors with X5R and X7R ceramic die lectrics are recommen ded because they are fairly stable over temperature.

The capacitors must also have a r ipple current rating greater than the maxi mum input ripple current of th e converter. The input r ipple current can be estimated as follows:

$$I_{CIN} = {}_{OUT} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times (1 - \frac{V_{OUT}}{I_{IN}})}$$
(13)

The worst-case condition occurs at:

$$I_{CIN} = \frac{I_{OUT}}{2}$$
(14)

For sim plification, cho ose the in put capacit or whose RMS current rating is greate r than half of the maximum load current.

The input capacitance value determines the input voltage ripple of the converter. If there is input voltage ripple requirement in the system design, choose the input capacitor that meets th e specification.

www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2012 MPS. All Rights Reserved. The input voltage ripple can be estimated as follows:

$$\Delta \Psi_{IN} = \frac{I_{OUT}}{F_{SV} \times I_{N}} \times \frac{V_{OUT}}{V_{IN}} \times 1 - \frac{V_{OUT}}{V_{IN}})$$
(15)

The worst-case condition occurs at $V_{IN} = 2V_{OUT}$, where:

$$\Delta \Psi_{\rm IN} = \frac{1}{4F} \frac{I_{\rm OUT}}{_{\rm SW} \times C_{\rm IN}}$$
(16)

Output Capacitor

The output capacitor is required to maintain the DC output voltage. Ceramic or POSCAP capacitors are recommended. The output voltage ripple can be estimated as:

$$\Delta \Psi_{\text{out}} = \frac{V_{\text{out}}}{F_{\text{SW}} \times \times} \times (1 - \frac{V_{\text{out}}}{V_{\text{IN}}}) \times (R_{\text{ESR}} + \frac{1}{8 - F_{\text{SW}} \times C_{\text{out}}}) (17)$$

Where R_{ESR} is the equivalent series resistance (ESR) of the output capacitor.

In the case of ceramic capacitors, the impedance at the switching frequency is dominated by the capacitance. The output voltage rip ple is mainly caused by the capacitance. For simplification, the output voltage ripple can be estimated as:

$$\Delta \Psi_{\text{OUT}} = \frac{V Y_{\text{UT}}}{8 \mathbb{K} \times_{\text{SW}}^2 L \times C_{\text{OUT}}} \times 1 - \frac{OUT}{V_{\text{IN}}})$$
(18)

The output voltage ripple caused by ESR is very small. Therefore, an external ramp is needed to stabilize the system. The volt age ramp is expected to be around 30mV. The e xternal ramp can be ge nerated thr ough resist or R4 and capacitor C4 using the following equation:

$$V_{\text{RAMP}} = \frac{(V_{\text{IN}} - \lambda V_{\text{OUT}}) T_{\text{ON}}}{R4 \times C4}$$
(19)

The C4 should be chosen so that it meets the following condition:

$$\frac{1}{2\mathbf{E} \times \mathbf{SW} \times \mathbf{C4}} < \frac{1}{5} \times (\frac{\mathbf{R}_1 \times \mathbf{R}_2}{\mathbf{R}_1 + \mathbf{R}_2})$$
(20)

In the case of POSCAP capacitor s, the ESR dominates the impedance at the switching frequency. The ramp voltage gene rated from the ESR is high enough to stabilize the system. Therefore, an external ramp is n ot needed. A minimum ESR value of 12m Ω is required to ensure sta ble operation of the converter. For simplification, the output ripple can b e approximated as:

$$\Delta \Psi_{OUT} = \frac{V_{OUT}}{F_{SW} \times L} \times (1 - \frac{V_{OUT}}{V_{IN}}) \times R_{ESR}$$
(21)

Inductor

The inductor is re quired to sup ply constan t current to the output load while be ing driven by the switch ing input voltage. A larger valu e inductor will result in less ripple cu rrent that will result in lower output ripple voltage. However, a larger value inductor will have a larger physical size, highe r series r esistance, and/or low er saturation current. A good rule for determining the inductor value is to allow the peak-to-peak ripple current in the ind uctor to be approximate ly 30~40% of the ma ximum switch current limit. Also, make sure that the peak inductor current is below the maxi mum switch current limit. The inductance value can be calculated as:

$$L = \frac{V_{OUT}}{F_{g_W} \times \Delta_L} \quad (1 - \frac{V_{OUT}}{V_{IN}})$$
(22)

Where ΔI_{L} is the peak-to-peak inductor ripple current.

Choose an inductor tha t will not sa turate under the maxi mum inductor peak curren t. The peak inductor current can be calculated as:

$$I_{L_{P}}^{I} = +_{OUT} \frac{V_{UT}^{Y}}{2F_{SW} \times L} \times (1 - \frac{OUT}{V_{IN}})$$
(23)

Part Number	Manufacturer	Inductance (µH)	DCR (mΩ)	Current Rating (A)	Dimensions L x W x H (mm³)	Switching Frequency (kHz)
PCMC-135T-R68MF	Cyntec	0.68	1.7	34	13.5 x 12.6 x 4.8	600
FDA1254-1R0M	токо	1	2	25.2	13.5 x 12.6 x 5.4	300~600
FDA1254-1R2M	токо	1.2	2.05	20.2	13.5 x 12.6 x 5.4	300~600

Table 1—Inductor Selection Guide

Typical Design Parameter Tables

The following tables include r ecommended component values for typical ou tput voltages (1.05V, 1.2V, 1.8V, 2. 5V, 3.3V) and switching frequencies (300kHz, 500kHz, and 700kHz). Refer to Tables 2-4 for design cases witho ut external ramp compensation and Tables 5-7 for design cases with external ramp compensation. needed when high-ESR External ra mp is not capacitors, such as electrolytic or POSCAPs are used. External ramp is needed when low-ESR capacitors, such as ceramic capacitors are used. For cases not listed in this datasheet, a calculator in excel spreadsheet can also be requested through a local sales representative to assist with the calculation.

Table 2—300kHz, $12V_{IN}$

V _{out} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R _{FREQ} (kΩ)
1.05 2	.2	12.1	43	301
1.2 2.	2	12.1	24	360
1.8 2.	2	19.6	15.8	499
2.5 2.	2	30	14.7	680
3.3 2.	2	40.2	13.3	806

Table 3—500kHz, $12V_{IN}$

V _{оит} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R _{FREQ} (kΩ)
1.05 1		12.1	43	180
1.2 1		12.1	24	200
1.8 1		19.6	15.8	309
2.5 1		30	14.7	402
3.3 1		40.2	13.3	523

Table 4—700kHz, $12V_{IN}$

V _{OUT} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R _{FREQ} (kΩ)
1.05	1 12.1		43	120
1.2 1		12.1	24	140
1.8 1		19.6	15.8	210
2.5 1		30	14.7	309
3.3 1		40.2	12.4	402

Table 5—300kHz, 12V_{IN}

V _{OUT} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R4 (kΩ)	C4 (pF)	R _{FREQ} (kΩ)
1.05	2.2 12	2.1	43	330	220	301
1.2	2.2 12	2.1	24	330	220	360
1.8	2.2 19	9.6	15.2	499	220	499
2.5	2.2	30 14	.7	499	220	680
3.3	2.2	40.2 1	3	604	220	806

Table 6—500kHz, $12V_{IN}$

V _{OUT} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R4 (kΩ)	C4 (pF)	R _{FREQ} (kΩ)
1.05	1 12	.1	43	330	220	180
1.2	1 12	.1	24	330	220	196
1.8	1 19	.6	15.8	330	220	309
2.5	1	30 14	.7	383	220	402
3.3	1	40.2 1	2	499	220	522

Table 7—700kHz, 12V_{IN}

	• • • • • • • • • • • • • • • • • • • •					
V _{OUT} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R4 (kΩ)	C4 (pF)	R _{FREQ} (kΩ)
1.05	1 12	.1	43	220	220	120
1.2	1 12	.1	24	220	220	140
1.8	1 19	.6	15.8	261	220	210
2.5	1 30		14.3	261	220	270
3.3	1 40	.2	12	360	220	383

TYPICAL APPLICATION



Figure 11 — Typical Application Circuit with Low ESR Ceramic Capacitor



Figure 12 — Typical Application Circuit with No External Ramp





LAYOUT RECOMMENDATION

- 1. The high current paths (GND, IN, and SW) should be placed very close to the device with short, direct and wide traces.
- 2. Put the input capacitor s as close to the I N and GND pins as possible.
- 3. Put the decoupling cap acitor as close to the V_{CC} and GND pins as possible.
- 4. Keep the switching no de SW short and away from the feedback network.
- 5. The external feedback resistor s should be placed next to the FB pin. Make sure that there is no via on the FB trace.
- 6. Keep the BST voltage path (BST, C_{BST} , and SW) as short as possible.
- 7. Keep the bottom IN and SW pads c onnected with large copper to achieve better thermal performance.
- 8. Four-layer layout is strongly recommended to achieve better thermal performance.



Top Layer



Inner1 Layer



Inner2 Layer



Figure 14—PCB Layout



PACKAGE INFORMATION



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